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APPLICATION NO.	FI	LING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/837,552	09/837,552 04/19/2001		Hisashi Ohtani	0756-2296	7555
22204	7590	02/13/2004		EXAMINER	
NIXON PE		•	RICHARDS	RICHARDS, N DREW	
401 9TH STREET, NW SUITE 900				ART UNIT	PAPER NUMBER
WASINGTO	ON, DC	20004-2128	2815		
				DATE MAILED: 02/13/2004	

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)	
	09/837,552	OHTANI ET AL.	
Office Action Summary	Examiner	Art Unit	
	N. Drew Richards	2815 Aw	
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the	correspondence address	
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period of Failure to reply within the set or extended period for reply will, by statute - Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b). Status	36(a). In no event, however, may a reply be ti y within the statutory minimum of thirty (30) da will apply and will expire SIX (6) MONTHS from , cause the application to become ABANDONE	mely filed ys will be considered timely. In the mailing date of this communication. ED (35 U.S.C. § 133).	
1) Responsive to communication(s) filed on <u>RCE</u>	and IDS filed 11/7/03.		
2a) ☐ This action is FINAL . 2b) ☒ This	action is non-final.		
3) Since this application is in condition for alloware closed in accordance with the practice under E			
Disposition of Claims			
4)	wn from consideration. <u>74</u> is/are allowed. s/are rejected.		
Application Papers			
9) The specification is objected to by the Examine 10) The drawing(s) filed on <u>08 November 2002</u> is/a Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the Examine 11.	re: a)⊠ accepted or b)⊡ object drawing(s) be held in abeyance. Se tion is required if the drawing(s) is ob	e 37 CFR 1.85(a). ojected to. See 37 CFR 1.121(d).	
Priority under 35 U.S.C. §§ 119 and 120	- mainaide	-) (d) (D	
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority application from the International Bureau * See the attached detailed Office action for a list 13) Acknowledgment is made of a claim for domesti since a specific reference was included in the first 37 CFR 1.78. a) The translation of the foreign language pro 14) Acknowledgment is made of a claim for domesti reference was included in the first sentence of the	s have been received. s have been received in Applicating documents have been received (PCT Rule 17.2(a)). of the certified copies not received priority under 35 U.S.C. § 1190 (st sentence of the specification of the priority under 35 U.S.C. § 120 (st priority under 35 U.S.C. §§ 12	ion Noed in this National Stage ed. (e) (to a provisional application) or in an Application Data Sheet. ceived. (c) and/or 121 since a specific	
Attachment(s)	_		
) ☑ Notice of References Cited (PTO-892) 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) ☑ Information Disclosure Statement(s) (PTO-1449) Paper No(s) 2:	5) Notice of Informal I	(PTO-413) Paper No(s) Patent Application (PTO-152)	

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DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.
- Claims 28, 34-36, 47, 48, 55-57, 64, 66 and 73 are rejected under 35
 U.S.C. 102(e) as being anticipated by Murade (U.S. Patent No. 6,330,044 B1).

With regard to claim 28, Murade discloses a semiconductor device including a CMOS circuit formed by an n-channel TFT and a p-channel TFT (CMOS with n-channel and p-channel TFT shown in figure 36(B)), wherein an active layer of the n-channel TFT is sandwiched by a first wiring line 7 and a second wiring line 43 through insulating layers 11,12 (figure 36(B), for example), wherein the active layer includes a low concentration impurity region 1d,1e (figure 27(B)) that is in contact with a channel formation region 1c, and wherein the low concentration impurity region is forme to overlap the fist wiring line and not to overlap the second wiring line. The specific transistor structure including the low concentration regions is shown in figure 27(B) for example, while the entire CMOS circuit is shown in figure 36(B) for example. In the specification, for example col. 29 lines 62-66, it is disclosed that the complementary TFT's (CMOS) can be formed in the same steps as the pixel TFT. Thus, the structure

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shown in figure 27(B) for the single transistor is disclosed as the same structure for each of the p-channel and n-channel transistors of the CMOS in figure 36(B).

With regard to claim 34, figure 27(B) shows the claimed structure in the pixel TFT where the low concentration impurity region overlaps the first wiring line and not the second wiring line.

With regard to claim 47, the device is one of an active matrix liquid crystal display and an active matrix EL display.

With regard to claim 55, Murade disclose a device having a pixel matrix circuit and a driver circuit formed on a same substrate, wherein each of the pixel TFT in the pixel matrix circuit and an n-channel TFT included in the driver circuit has a structure including an active layer sandwiched by each of a first wiring line and a second wiring line through insulating layers (pixel TFT shown in figure 27(B), n-channel driver TFT shown in figure 36(B)), each of the active layers includes a low concentration impurity region that is in contact with each of channel formation regions, and each of the low concentration impurity regions is formed to overlap each of the first wiring lines and not to overlap each of the second wiring lines. With regard to the limitations of the potentials applied to the wiring lines, these limitations are merely intended use limitations that do not structurally distinguish over the prior art. The device of Murade is capable of having the claimed potentials applied.

With regard to claim 56, the device is an active matrix liquid crystal display device.

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With regard to claims 64, 66 and 73, at least one of the first wiring layer and the second wiring layer is disclosed as containing an element selected from the group of Ta, Ti, W, Mo or Si.

With regard to claim 35, 36, 48 and 57 the limitations of these claims of keeping the first and second wiring lines at certain potentials are intended use limitations that do not structurally distinguish over the prior art. The device of Murade is capable of having the claimed electric potentials applied to the first and second wiring line and thus reads on the claims.

Allowable Subject Matter

- 3. Claims 30-33, 37-41, 45, 58-63, 65, 67-71 and 74 are allowed.
- 4. Claims 29 and 72 objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.
- 5. The following is a statement of reasons for the indication of allowable subject matter: Prior art of record fails to teach, disclose, or suggest, either alone or in combination, (1) a TFT having an active layer sandwiched by a first wiring line and a second wiring line where the second wiring line has a portion being a laminate of a first conductive layer and a second conductive layer and a portion being a laminate of the first conductive layer, the second conductive layer, and a third conductive layer or (2) a TFT having an active layer sandwiched by a first wiring layer and a second wiring layer,

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where a low concentration impurity region in contact with the channel overlaps the first wiring line but not the second wiring line, and the first and second wiring line are electrically connected.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to N. Drew Richards whose telephone number is (571) 272-1736. The examiner can normally be reached on M-F 8:00-5:30; Every other Friday off.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on (571) 272-1664. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

ns OM **Supervisory Patent Examiner**

Technology Center 2800